

# BSR58LT1

## JFET Chopper Transistor

### N-Channel – Depletion

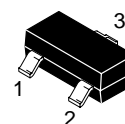
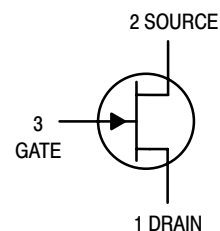


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#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain–Gate Voltage	$V_{DG}$	–40	Vdc
Gate–Source Voltage	$V_{GS}$	–35	Vdc
Gate Current	$I_G$	50	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	350 2.8	mW mW/ $^\circ\text{C}$
Lead Temperature	$T_L$	300	$^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	–65 to +150	$^\circ\text{C}$



SOT–23  
CASE 318  
STYLE 10

#### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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#### OFF CHARACTERISTICS

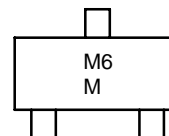
Gate–Source Breakdown Voltage ( $I_G = -1.0 \mu\text{Adc}$ )	$V_{(BR)GSS}$	40	–	Vdc
Gate Reverse Current ( $V_{GS} = -15 \text{ Vdc}$ )	$I_{GSS}$	–	–1.0	nAdc
Gate Source Cutoff Voltage ( $V_{DS} = 5.0 \text{ Vdc}$ , $I_D = 1.0 \mu\text{Adc}$ )	$V_{GS(off)}$	–0.8	–4.0	Vdc
Drain–Cutoff Current ( $V_{DS} = 5.0 \text{ Vdc}$ , $V_{GS} = -10 \text{ Vdc}$ )	$I_{D(off)}$	–	1.0	nAdc

#### ON CHARACTERISTICS

Zero–Gate–Voltage Drain Current (Note 1) ( $V_{DS} = 15 \text{ Vdc}$ )	$I_{DSS}$	8.0	80	mAdc
Static Drain–Source On Resistance ( $V_{DS} = 0.1 \text{ Vdc}$ )	$r_{DS(on)}$	–	60	$\Omega$
Drain Gate and Source Gate On–Capacitance ( $V_{DS} = V_{GS} = 0$ , $f = 1.0 \text{ MHz}$ )	$C_{dg(on)}$ + $C_{sg(on)}$	–	28	pF
Drain Gate Off–Capacitance ( $V_{GS} = -10 \text{ Vdc}$ , $f = 1.0 \text{ MHz}$ )	$C_{dg(off)}$	–	5.0	pF
Source Gate Off–Capacitance ( $V_{GS} = -10 \text{ Vdc}$ , $f = 1.0 \text{ MHz}$ )	$C_{sg(off)}$	–	5.0	pF

1. Pulse Width = 300  $\mu\text{s}$ , Duty Cycle = 3.0%.

#### MARKING DIAGRAM



M6 = Specific Device Code  
M = Date Code

#### ORDERING INFORMATION

Device	Package	Shipping
BSR58LT1	SOT–23	3000/Tape & Reel

## TYPICAL SWITCHING CHARACTERISTICS

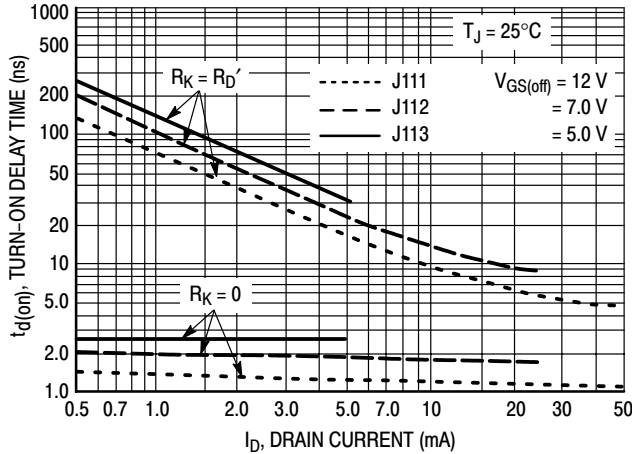


Figure 1. Turn-On Delay Time

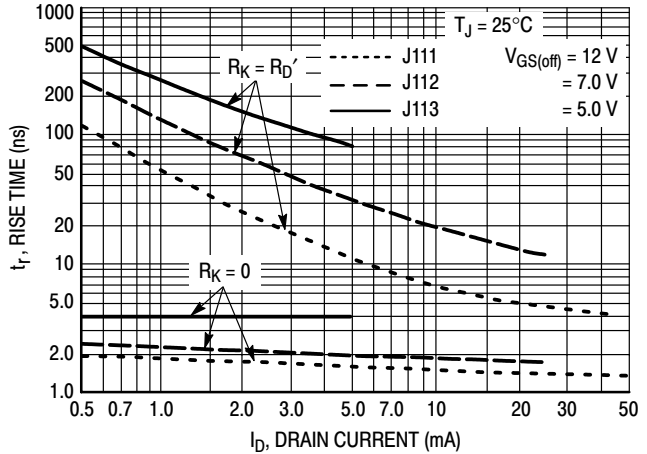


Figure 2. Rise Time

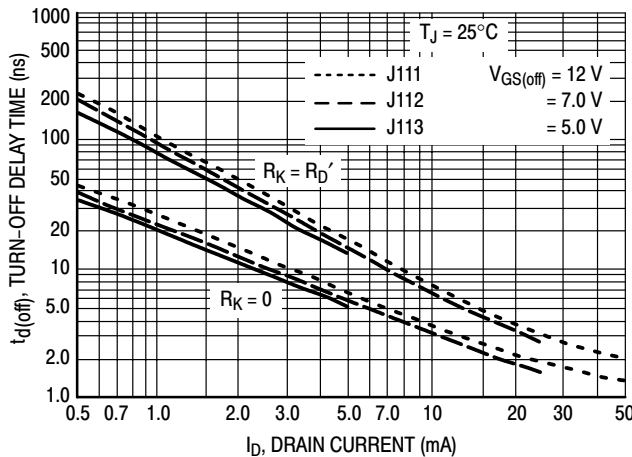


Figure 3. Turn-Off Delay Time

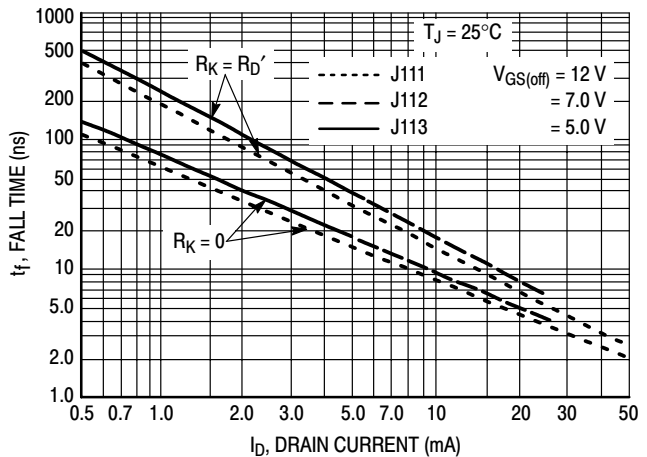


Figure 4. Fall Time

## NOTE 1

The switching characteristics shown above were measured using a test circuit similar to Figure 5. At the beginning of the switching interval, the gate voltage is at Gate Supply Voltage ( $-V_{GG}$ ). The Drain-Source Voltage ( $V_{DS}$ ) is slightly lower than Drain Supply Voltage ( $V_{DD}$ ) due to the voltage divider. Thus Reverse Transfer Capacitance ( $C_{rss}$ ) or Gate-Drain Capacitance ( $C_{gd}$ ) is charged to  $V_{GG} + V_{DS}$ .

During the turn-on interval, Gate-Source Capacitance ( $C_{gs}$ ) discharges through the series combination of  $R_{GEN}$  and  $R_K$ .  $C_{gd}$  must discharge to  $V_{DS(on)}$  through  $R_G$  and  $R_K$  in series with the parallel combination of effective load impedance ( $R'_D$ ) and Drain-Source Resistance ( $r_{ds}$ ). During the turn-off, this charge flow is reversed.

Predicting turn-on time is somewhat difficult as the channel resistance  $r_{ds}$  is a function of the gate-source voltage. While  $C_{gs}$  discharges,  $V_{GS}$  approaches zero and  $r_{ds}$  decreases. Since  $C_{gd}$  discharges through  $r_{ds}$ , turn-on time is non-linear. During turn-off, the situation is reversed with  $r_{ds}$  increasing as  $C_{gd}$  charges.

The above switching curves show two impedance conditions; 1)  $R_K$  is equal to  $R_D$ , which simulates the switching behavior of cascaded stages where the driving source impedance is normally the load impedance of the previous stage, and 2)  $R_K = 0$  (low impedance) the driving source impedance is that of the generator.

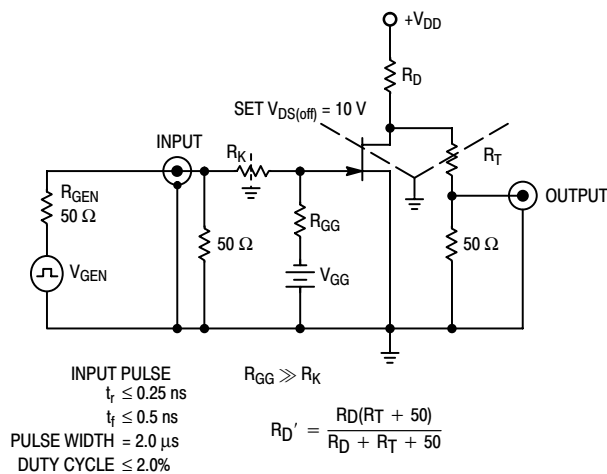


Figure 5. Switching Time Test Circuit

# BSR58LT1

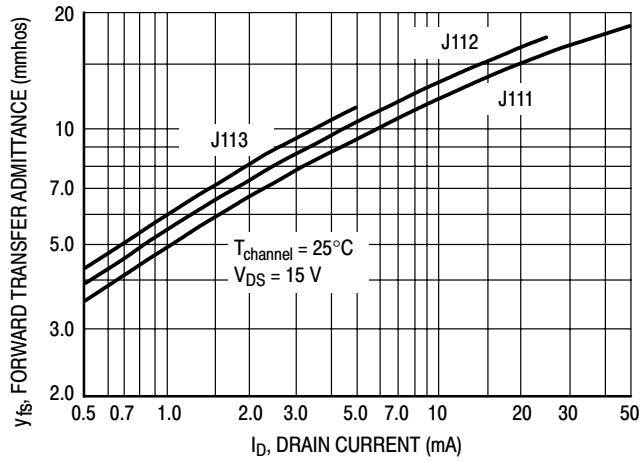


Figure 6. Typical Forward Transfer Admittance

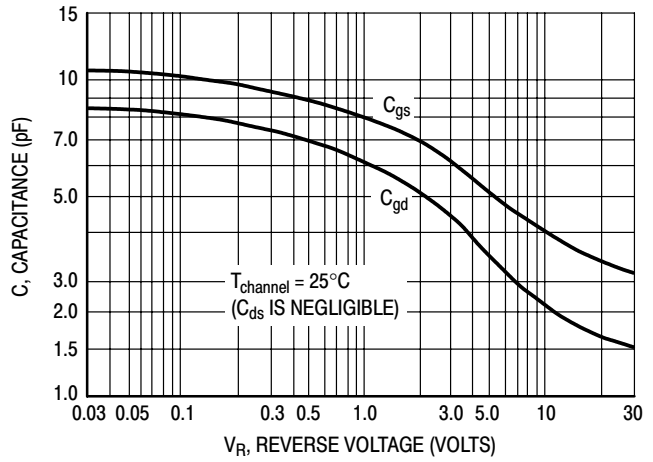


Figure 7. Typical Capacitance

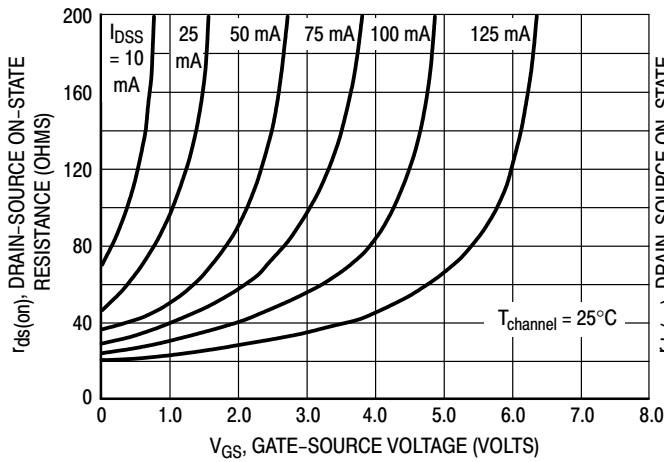


Figure 8. Effect of Gate-Source Voltage On Drain-Source Resistance

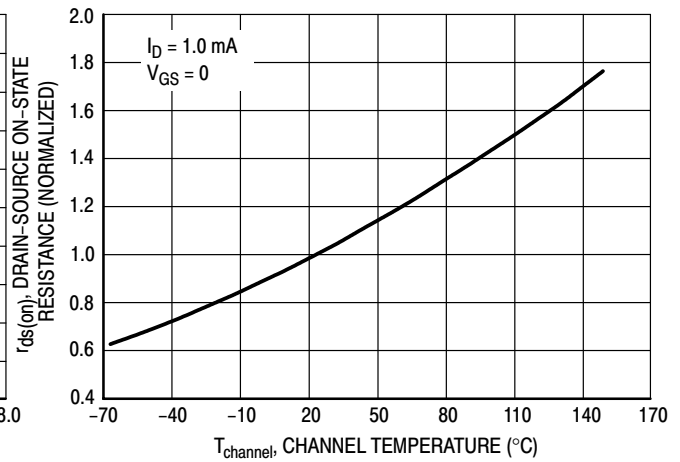


Figure 9. Effect of Temperature On Drain-Source On-State Resistance

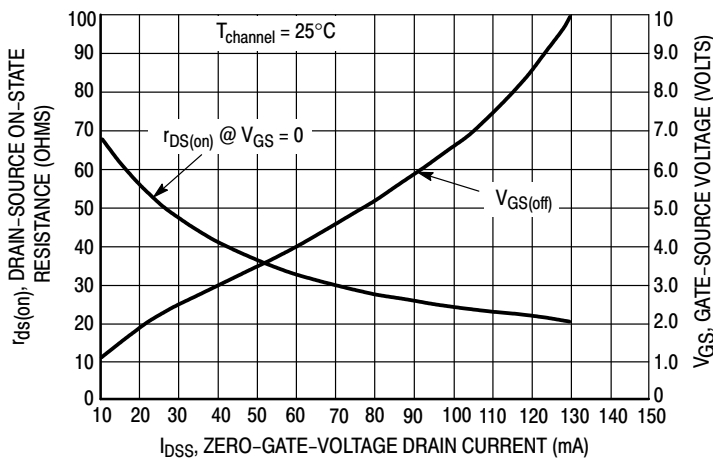


Figure 10. Effect of  $I_{DSS}$  On Drain-Source Resistance and Gate-Source Voltage

## NOTE 2

The Zero-Gate-Voltage Drain Current ( $I_{DSS}$ ), is the principle determinant of other J-FET characteristics. Figure 10 shows the relationship of Gate-Source Off Voltage ( $V_{GS(off)}$ ) and Drain-Source On Resistance ( $r_{ds(on)}$ ) to  $I_{DSS}$ . Most of the devices will be within  $\pm 10\%$  of the values shown in Figure 10. This data will be useful in predicting the characteristic variations for a given part number.

For example:

Unknown

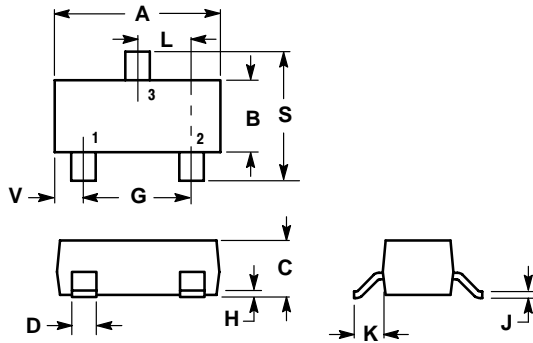
$r_{ds(on)}$  and  $V_{GS}$  range for an J112

The electrical characteristics table indicates that an J112 has an  $I_{DSS}$  range of 25 to 75 mA. Figure 10, shows  $r_{ds(on)} = 52$  Ohms for  $I_{DSS} = 25$  mA and 30 Ohms for  $I_{DSS} = 75$  mA. The corresponding  $V_{GS}$  values are 2.2 volts and 4.8 volts.

# BSR58LT1

## PACKAGE DIMENSIONS

### SOT-23 (TO-236) CASE 318-08 ISSUE AH




#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

#### STYLE 10:

1. DRAIN
2. SOURCE
3. GATE

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